High-Mobility InSe Transistors: The Role of Surface Oxi

ACS Nano

11, 7362-7370

DOI: 10.1021/acsnano.7b03531

Citation Report

#	Article	IF	Citations
4	Scalable van der Waals Heterojunctions for High-Performance Photodetectors. ACS Applied Materials & Interfaces, 2017, 9, 36181-36188.	4.0	29
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